## IN THE CLAIMS

1 (Previously Presented). A method comprising:

forming a pore in an insulator;

forming a sidewall spacer in said pore;

forming a heater in said pore with said sidewall spacer;

removing an upper portion of said heater to form a gap;

filling the gap with a phase change material that extends over said insulator; and

patterning and etching said phase change material over said insulator.

Claims 2 and 3 (Canceled).

4 (Previously Presented). The method of claim 1 including planarizing the upper surface of said insulator.

Claims 5, 6, and 7 (Canceled).

8 (Previously Presented). The method of claim 1 including forming a T-shaped phase change material.

Claim 9 (Canceled).

10 (Previously Presented). The method of claim 9 wherein forming a heater includes depositing metal in said pore after forming said sidewall spacer.

Claims 11-31 (Canceled).

32 (Previously Presented). The method of claim 1 including using said spacer to reduce a lateral dimension of said pore to a sublithographic dimension.

33 (Previously Presented). A method comprising:

forming a pore, having sublithographic dimensions, said pore formed in an insulator;

filling said sublithographic pore with a heater;

removing the upper portion of said heater to form a gap;

filling the gap with a phase change material that extends over said insulator; and

patterning and etching said phase change material over said insulator.

34 (Previously Presented). The method of claim 33 including planarizing the upper surface of said insulator.

35 (Previously Presented). The method of claim 33 including forming a T-shaped phase change material.

36 (Previously Presented). The method of claim 35 wherein forming a heater includes depositing metal in said pore after forming said sidewall spacer.

37 (Previously Presented). The method of claim 33 wherein forming a pore includes forming a trench in an insulator and lining said trench with a sidewall spacer.